

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRF314** is Designed for Class C Power Amplifier Applications up to 200 MHz.

FEATURES:

- $P_G = 10$ dB min. at 30 W/ 150 MHz
- Withstands **30:1** Load VSWR
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.4 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	82 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.13 °C/W

PACKAGE STYLE .380 4L FLG

	MS00004 FOR REFERENCE	MS00004 FOR REFERENCE
A	208/13.93	208/13.93
B	286/19.94	286/19.94
C	158/10.09	158/10.04
D	370/24.44	368/24.30
E	388/25.16	388/25.16
F	304/19.13	304/19.13
G	388/25.16	375/23.81
H	140/9.00	138/9.51
I		286/22.1
J	242/15.31	235/14.80

ORDER CODE: ASI10872

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 30$ mA	35			V
BV_{CES}	$I_C = 30$ mA	65			V
BV_{EBO}	$I_E = 3.0$ mA	4.0			V
I_{CBO}	$V_E = 30$ V			3.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.5$ A	20		80	---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz		30	40	pF
P_G	$V_{CC} = 28$ V $P_{OUT} = 30$ W $f = 150$ MHz	10	13.5		dB
η_c		50			%
ψ		30:1 all phase angles, no degradation in output.			

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